# III B.Tech - II Semester - Regular/Supplementary Examinations AUGUST 2021 

## VLSI DESIGN (ELECTRONICS \& COMMUNICATION ENGINEERING)

Duration: 3 hours
Max. Marks: 70
PART - A

Answer all the questions. All questions carry equal marks $11 \mathrm{x} 2=22 \mathrm{M}$
1.
a) Define propagation delay of a CMOS inverter.
b) Define body bias effect.
c) Define any two layout design rules.
d) Give expression for propagation delay of an inverter.
e) What is constant electric field scaling?
f) Write short notes on transmission gate.
g) What is semicustom design?
h) Short notes on standard cell-based PLD?
i) What is the need for testing?
j) What is the principle behind logic verification?
k) What is latch-up? How to prevent latch-up?
PART - B

Answer any THREE questions. All questions carry equal marks.

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3 \times 16=48 \mathrm{M}
$$

2. a) Describe the equation for source to drain current in the three regions of operation of a MOS transistor and draw the V-I characteristics.
b) Explain the DC transfer characteristics of a CMOS Inverter with necessary conditions for the three different regions of operation.
3. a) Derive an expression for the rise time, fall time, and propagation delay of a CMOS inverter.
b) Discuss in detail with a neat layout, the design rules for a CMOS inverter.

## 4. a) Derive the scaling factors of MOS device.

b) Discuss the limitation of interconnects and contact resistance scaling.
5. a) Implement full subtractor using PLA and PAL. 8 M
b) Draw and explain the Xilinx FPGA architecture. 8 M
6. a) Explain the principle of Built-In Self-Test (BIST). What are the advantages and disadvantages of BIST? 8 M
b) Explain what is meant by a Stuck-at-1 fault and a Stuck-at-0 fault with suitable example.

